

SANYO	No.3485	2SC4694
		NPN Epitaxial Planar Silicon Transistor Low-Frequency General-Purpose Amp, Muting Applications

Features

- Adoption of FBET process
- High DC current gain
- High V_{EBO} ($V_{EBO} \geq 25V$)
- High reverse h_{FE} (150 typ)
- Small ON resistance [$R_{on} = 1\Omega$ ($I_B = 5mA$)]
- Very small-sized package permitting 2SC4694-applied sets to be made small and slim

Absolute Maximum Ratings at $T_a = 25^\circ C$

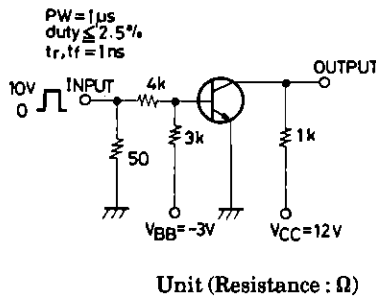
			unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	25	V
Collector Current	I_C	500	mA
Collector Current(Pulse)	I_{CP}	800	mA
Base Current	I_B	100	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

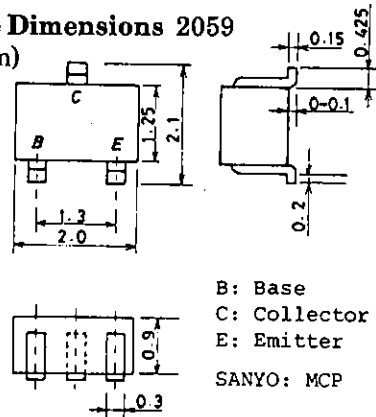
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 20V, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 10mA$	300		1200	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 10mA$		250		MHz
Output Capacitance	c_{ob}	$V_{CB} = 10V, f = 1MHz$		3.6		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.12	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	25			V
Turn-ON time	t_{on}	See specified Test Circuit.		135		ns
Storage Time	t_{stg}	See specified Test Circuit.		450		ns
Fall Time	t_f	See specified Test Circuit.		100		ns

Marking : WT

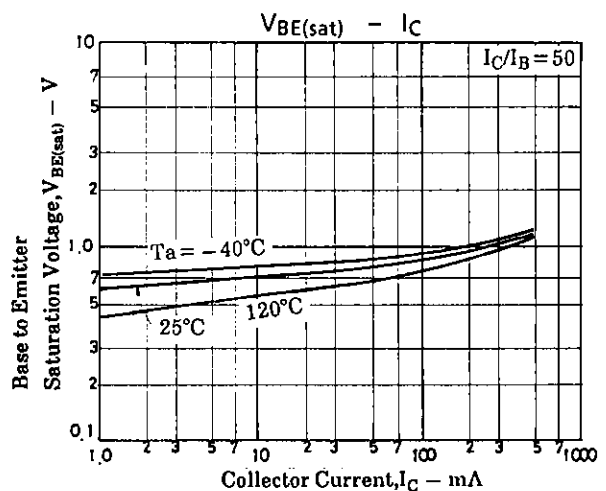
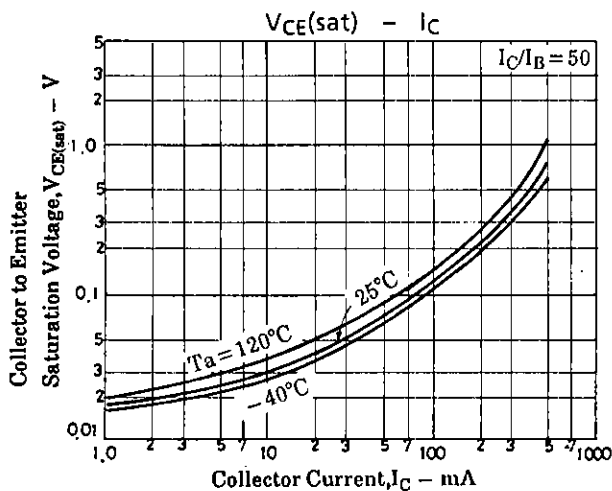
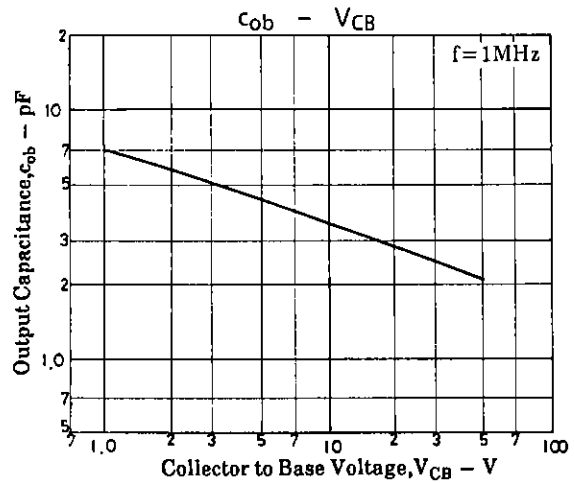
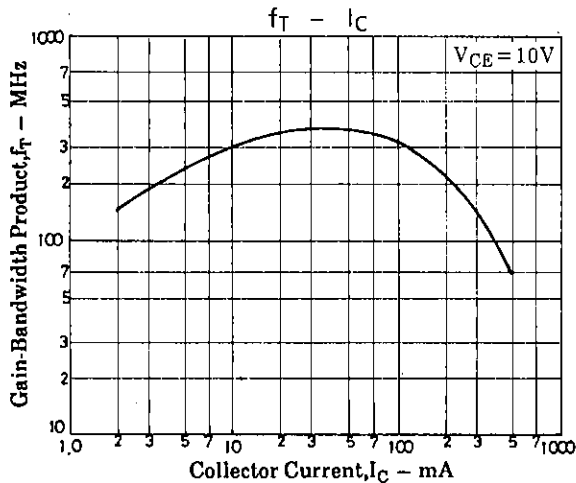
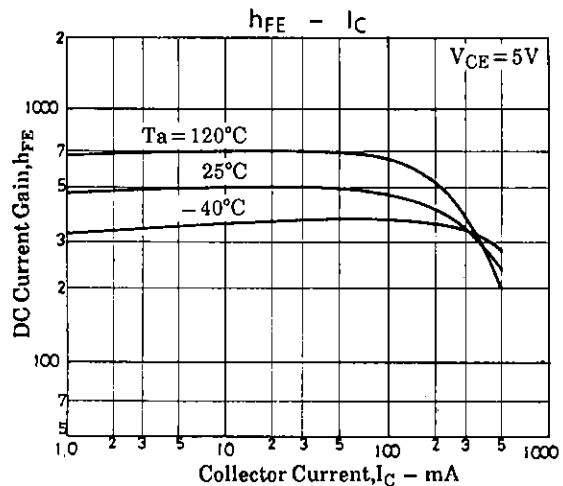
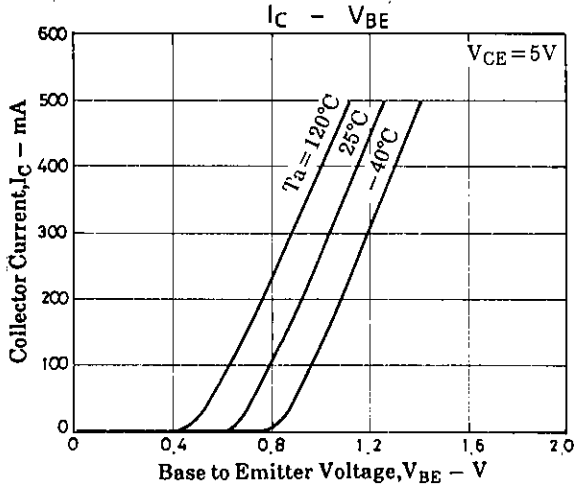
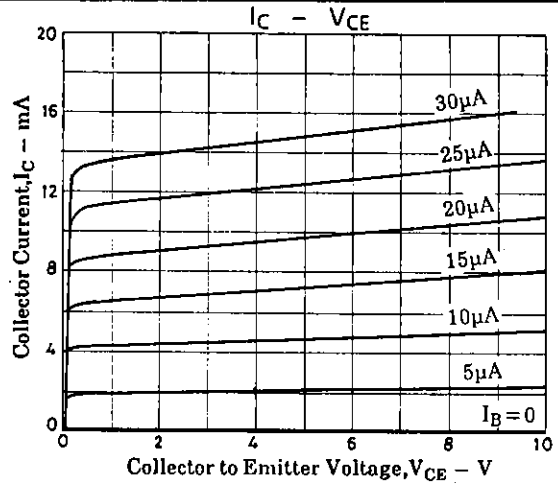
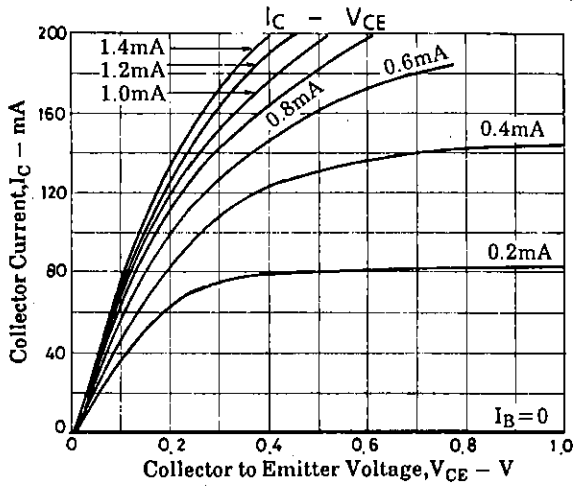
Switching Time Test Circuit

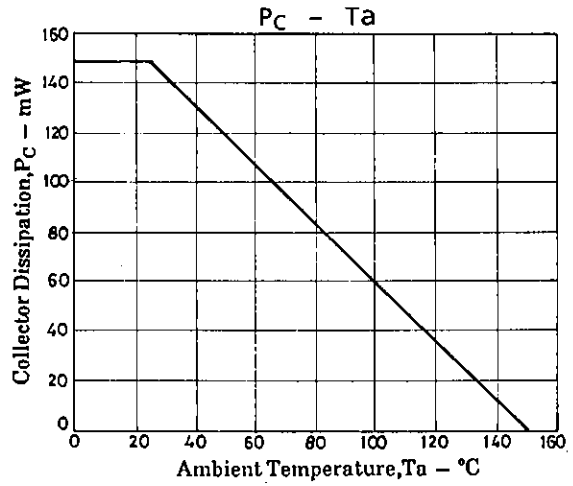
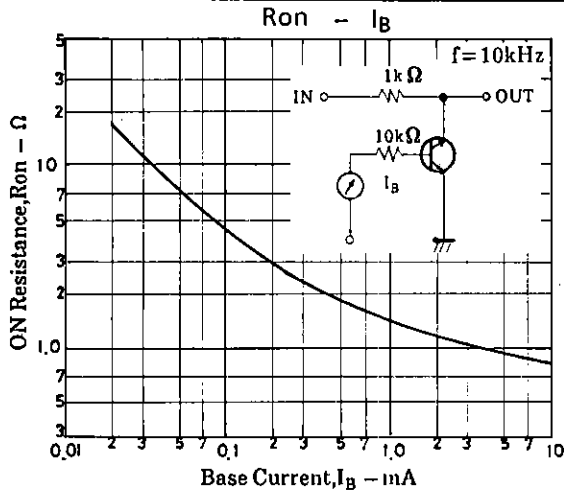


Package Dimensions 2059
(unit : mm)



2SC4694





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